

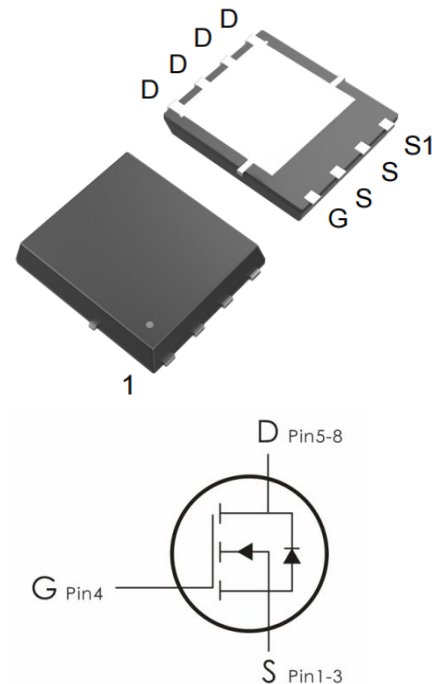
Description:

This N-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=40V, I_D=140A, R_{DS(ON)}<2m\Omega @V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DON140N04	140N04	DFN5*6-8	5000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	140	A
I_{DM}	Pulsed Drain Current	560	
P_D	Power Dissipation	83	W
E_{AS}	Single pulse avalanche energy	200	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^{\circ}C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.5	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	20	$^{\circ}C/W$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	40	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =40V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1	---	2.5	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =10V, I _D =20A	---	1.65	2	m Ω
		V _{GS} =4.5V, I _D =20A	---	2.8	3.5	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	3829	---	pF
C _{oss}	Output Capacitance		---	2793	--	
C _{rss}	Reverse Transfer Capacitance		---	473	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =20V R _{ENG} =10 Ω	---	892.7	---	ns
t _r	Rise Time		---	21.3	---	ns
t _{d(off)}	Turn-Off Delay Time		---	72.27	---	ns
t _f	Fall Time		---	34.51	---	ns
Q _g	Total Gate Charge	V _{DS} =32V, I _D =10A	---	65	---	nc
Q _{gs}	Gate-Source Charge		---	13.5	---	nc
Q _{gd}	Gate-Drain “Miller” Charge		---	12.5	---	nc
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =20A	---	---	0.78	V
I _S	Continuous Drain Curren	VD=VG=0V	---	---	140	A
I _{SM}	Pulsed Drain Current		---	---	560	A
T _{rr}	Reverse Recovery Time	I _F =1A, T _J =25 °C	---	31	---	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/us	---	110	---	nc

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_D=32\text{V}$, $L=0.5\text{mH}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

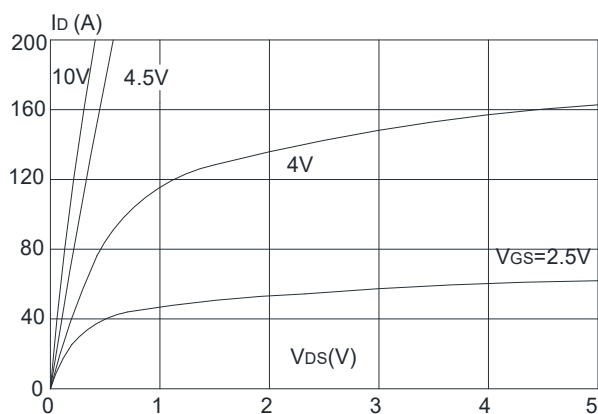


Figure1: Output Characteristics

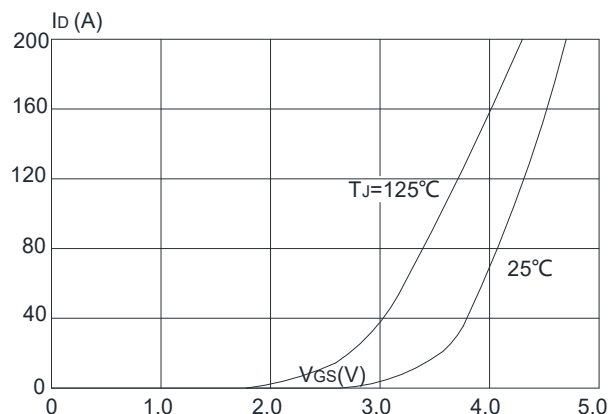


Figure 2: Typical Transfer Characteristics

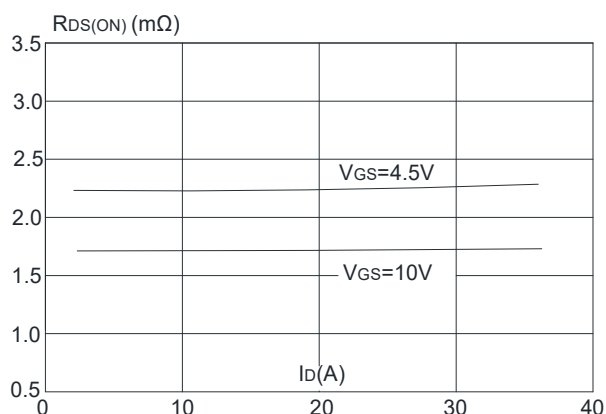


Figure 3: On-resistance vs. Drain Current

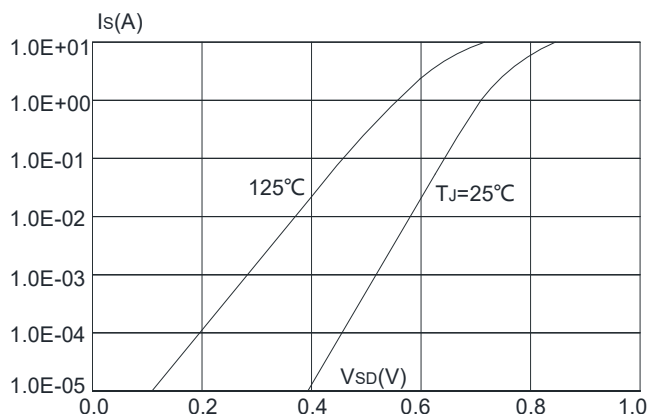


Figure 4: Body Diode Characteristics

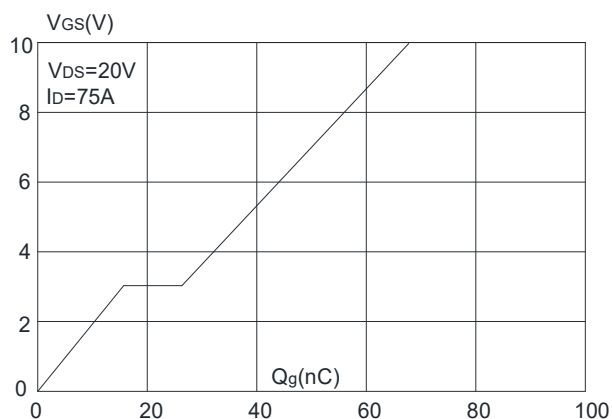


Figure 5: Gate Charge Characteristics

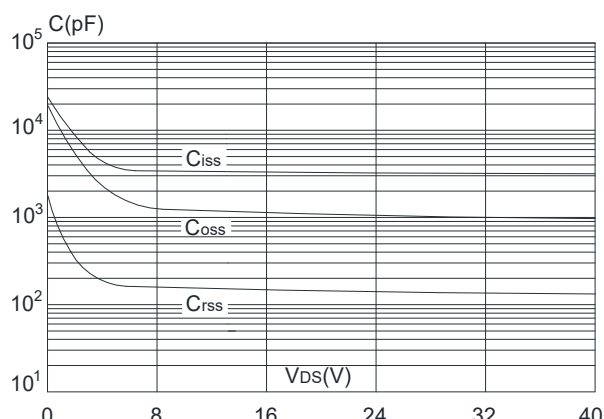


Figure 6: Capacitance Characteristics

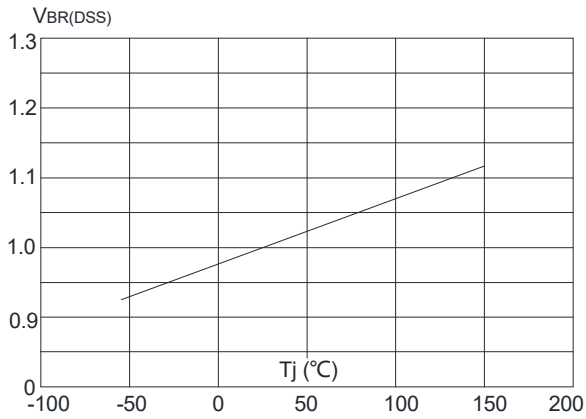


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

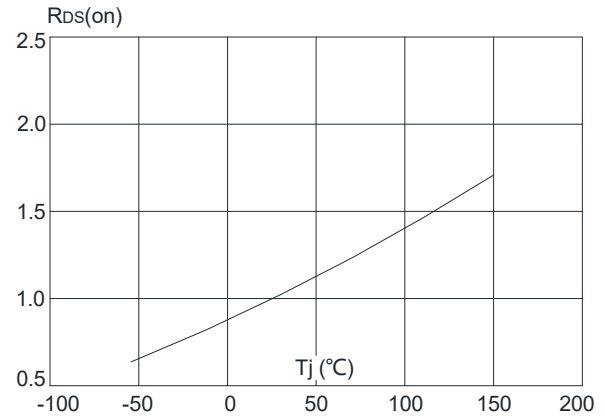


Figure 8: Normalized on Resistance vs. Junction Temperature

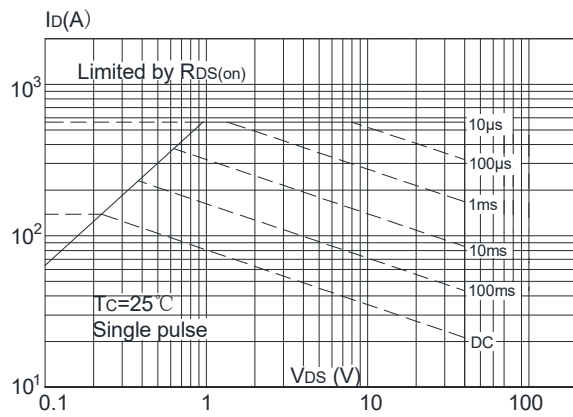


Figure 9: Maximum Safe Operating Area

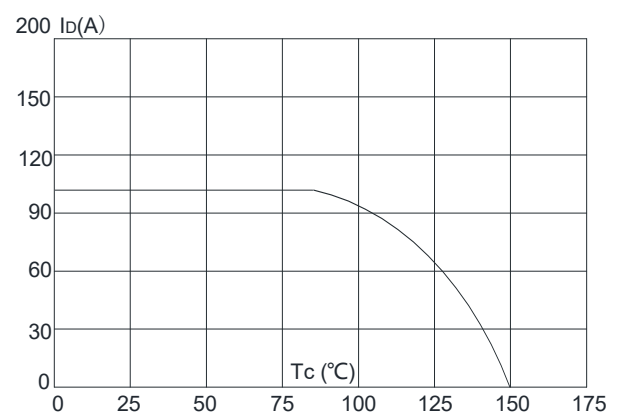


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

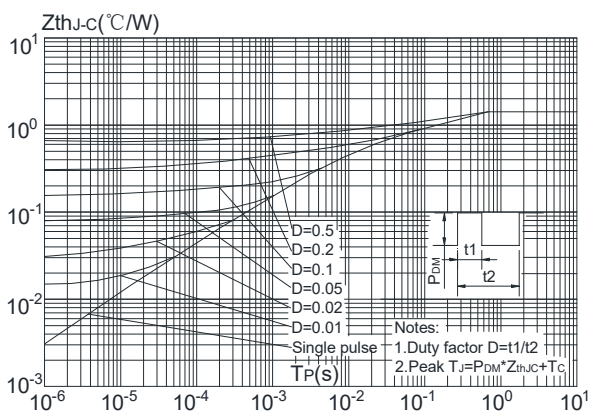
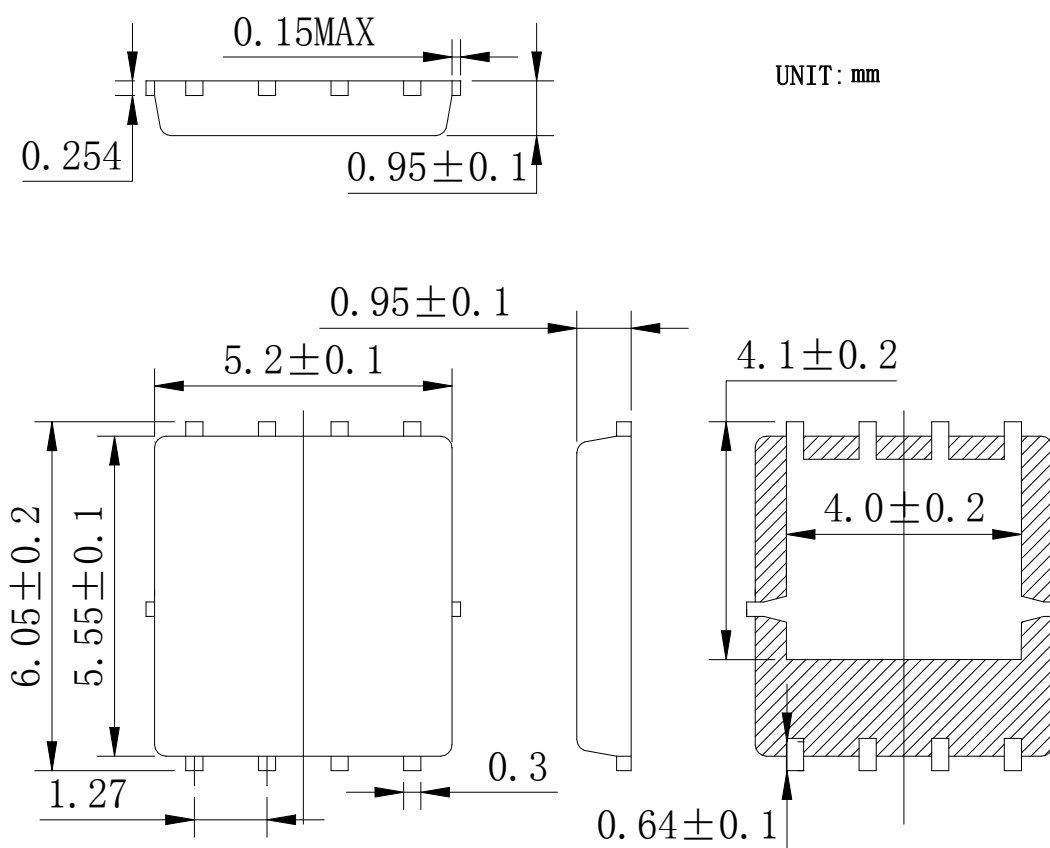


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

DFN5x6-8 Package Information:



Marking Information:

①. Doingter LOGO

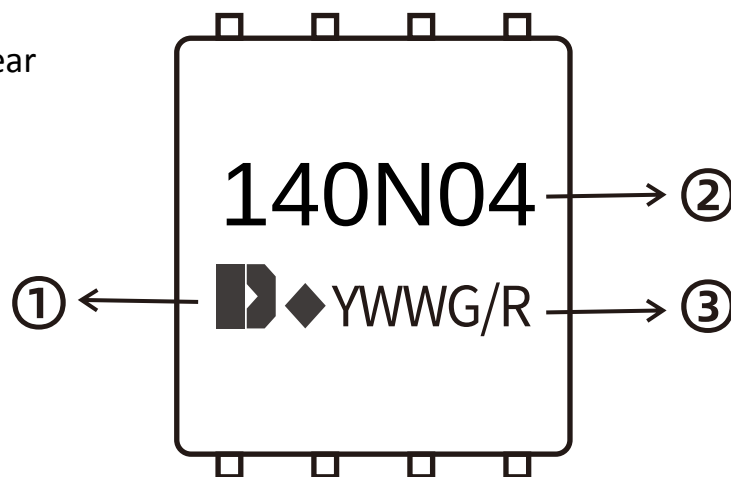
②. Part NO.

③. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



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